



PSMN011-60MS

N-channel 60 V 11.3 m Ω standard level MOSFET in LFPAK33

4 June 2013

Product data sheet

1. General description

Standard level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources
- LFPAK33 package is footprint compatible with other 3.3mm types
- Qualified to 175 °C

3. Applications

- AC-to-DC converters
- Synchronous rectification
- DC-DC converters

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C	-	-	60	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; Fig. 1	-	-	61	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 2	-	-	91	W
T _j	junction temperature		-55	-	175	°C
Static characteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 12	-	9.6	11.3	m Ω
Dynamic characteristics						
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 15 A; V _{DS} = 30 V; T _j = 25 °C; Fig. 14 ; Fig. 15	-	5.8	-	nC

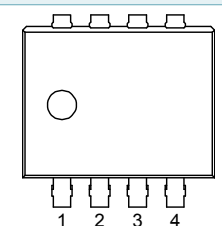
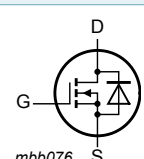


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFAK33 (SOT1210)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PSMN011-60MS	LFAK33	Plastic single ended surface mounted package (LFAK33); 4 leads	SOT1210

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN011-60MS	M11S60

8. Limiting values

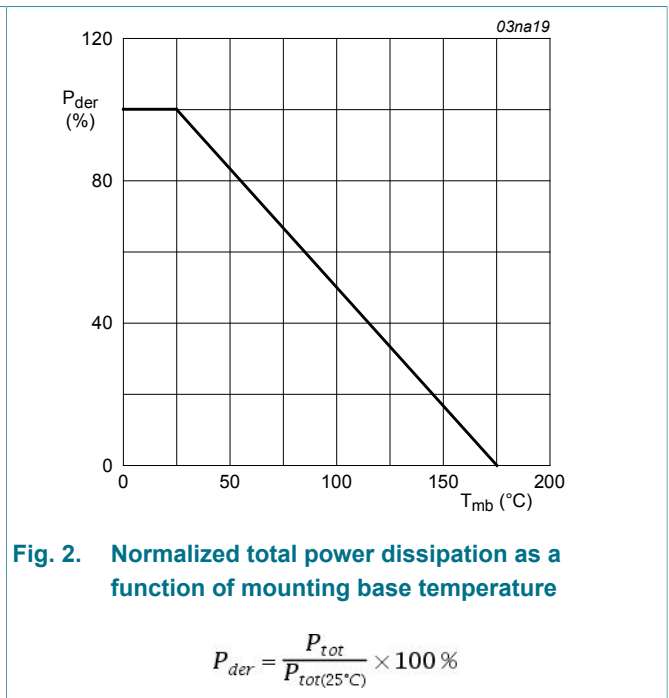
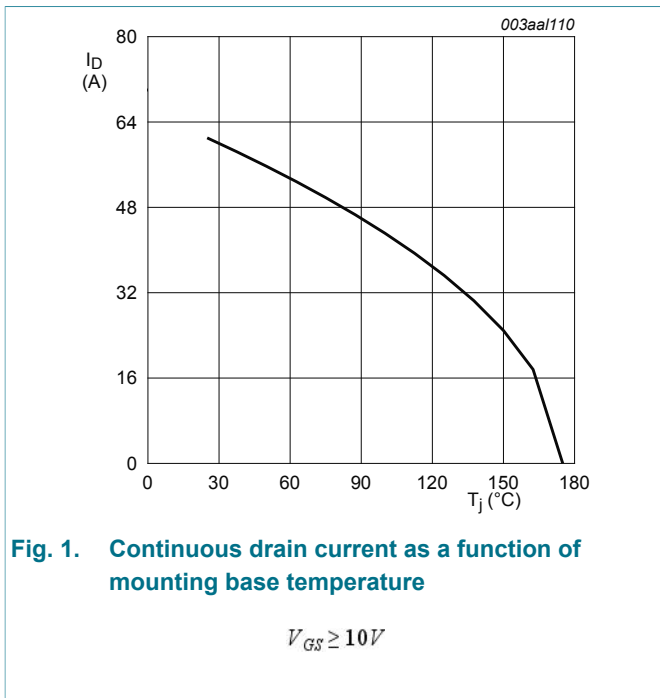
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$	-	60	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}; \text{Fig. 1}$	-	61	A
		$V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C}; \text{Fig. 1}$	-	43	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}; T_{mb} = 25\text{ °C}; \text{Fig. 4}$	-	244	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 2}$	-	91	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C

Symbol	Parameter	Conditions		Min	Max	Unit
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ °C}$	[1]	-	70	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$		-	244	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 61\text{ A}$; $V_{sup} \leq 60\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped; Fig. 3		-	48.1	mJ

[1] Continuous current is limited by package



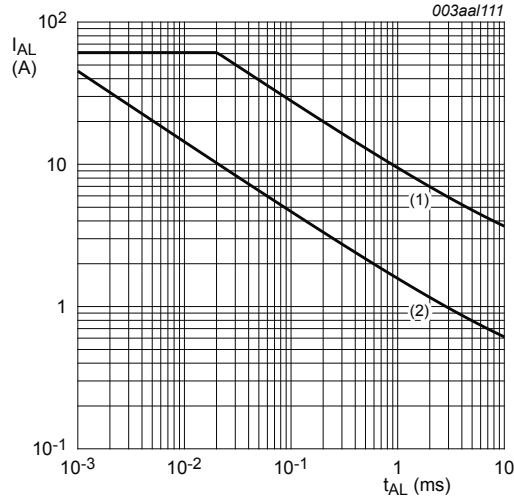


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j (init)} = 25^{\circ}C$; (2) $T_{j (init)} = 100^{\circ}C$

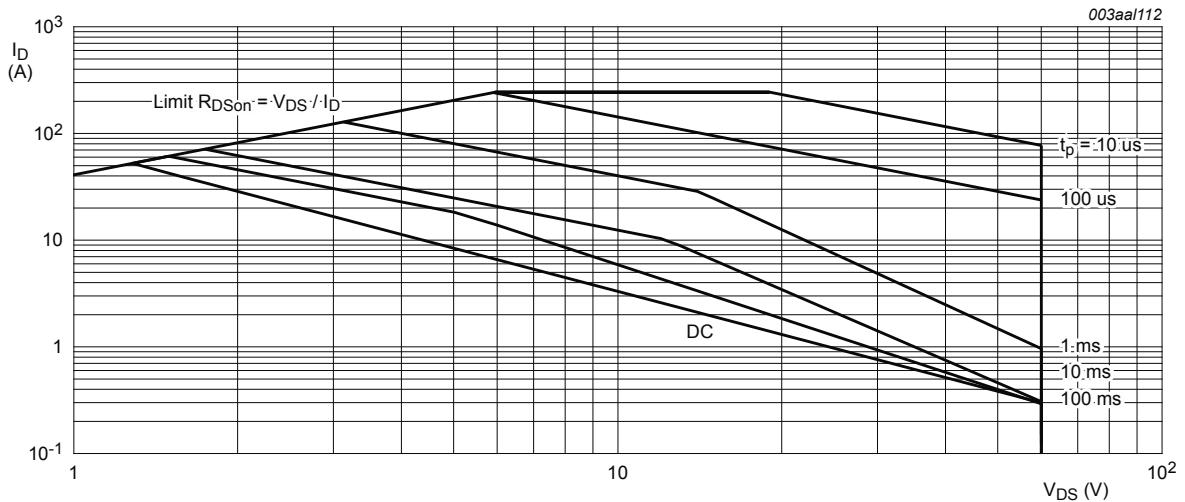


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	1.44	1.65	K/W

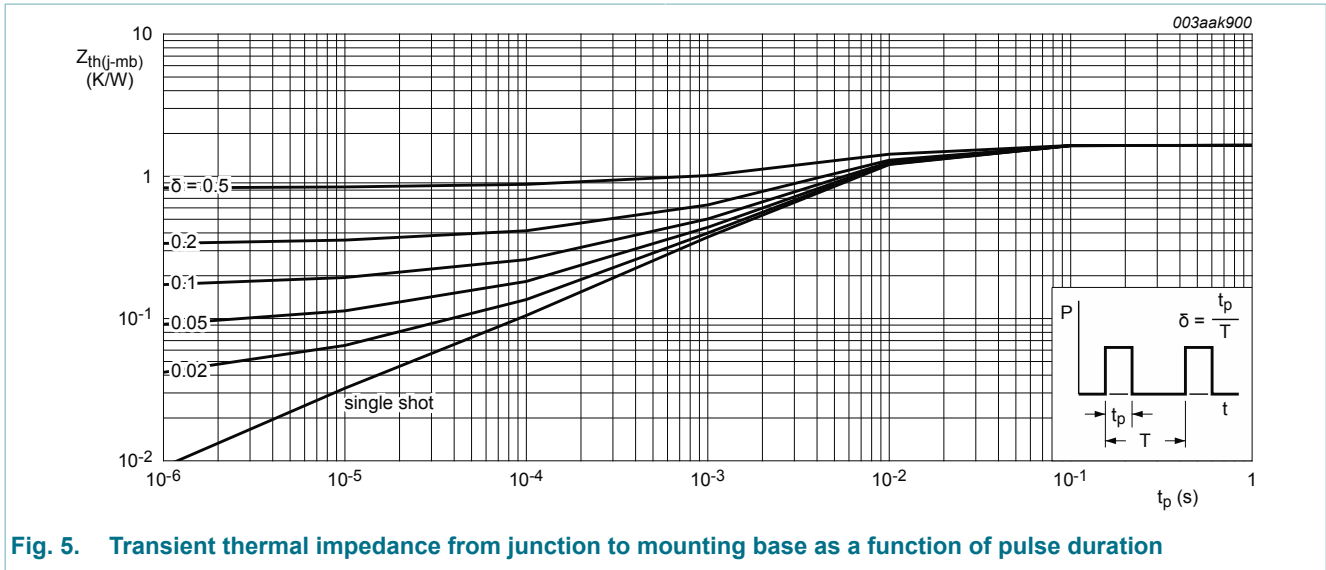


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	60	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	54	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C$; Fig. 10	1	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$; Fig. 10 ; Fig. 11	2.3	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$; Fig. 10	-	-	4.6	V
I_{DSS}	drain leakage current	$V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.054	1	μA
		$V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 15 A; T_j = 25 \text{ }^\circ C$; Fig. 12	-	9.6	11.3	mΩ
		$V_{GS} = 10 V; I_D = 15 A; T_j = 175 \text{ }^\circ C$; Fig. 13	-	-	24.4	mΩ
R_G	gate resistance	$f = 1 \text{ MHz}$	-	2.75	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 15 A; V_{DS} = 30 V; V_{GS} = 10 V$; $T_j = 25 \text{ }^\circ C$; Fig. 14 ; Fig. 15	-	23	-	nC

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Q_{GS}	gate-source charge	$I_D = 15\text{ A}; V_{DS} = 30\text{ V}; V_{GS} = 10\text{ V};$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 14 ; Fig. 15	-	6.1	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	3.9	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	2.2	-	nC
Q_{GD}	gate-drain charge		-	5.8	-	nC
C_{iss}	input capacitance	$V_{DS} = 30\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 16	-	1368	-	pF
C_{oss}	output capacitance		-	191	-	pF
C_{rss}	reverse transfer capacitance		-	108	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30\text{ V}; R_L = 2\text{ }^\Omega; V_{GS} = 10\text{ V};$ $R_{G(ext)} = 5\text{ }^\Omega; T_j = 25\text{ }^\circ\text{C}$	-	6.7	-	ns
t_r	rise time		-	8.46	-	ns
$t_{d(off)}$	turn-off delay time		-	16.9	-	ns
t_f	fall time		-	9.18	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 15\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 17	-	0.84	1.2	V
t_{rr}	reverse recovery time	$I_S = 15\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$	-	21.7	-	ns
Q_r	recovered charge	$V_{DS} = 30\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	19.2	-	nC

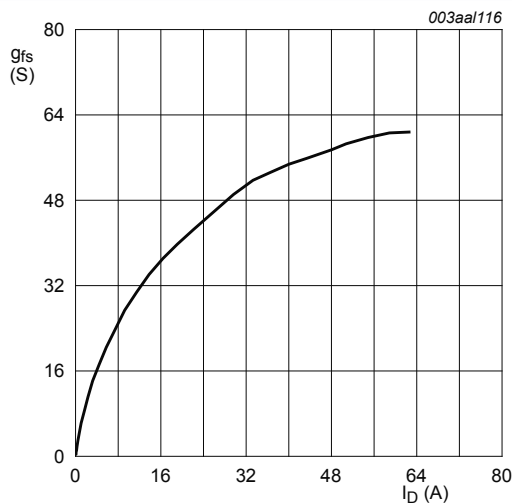


Fig. 6. Forward transconductance as a function of drain current; typical values

$T_j = 25^\circ\text{C}; V_{DS} = 10\text{V}$

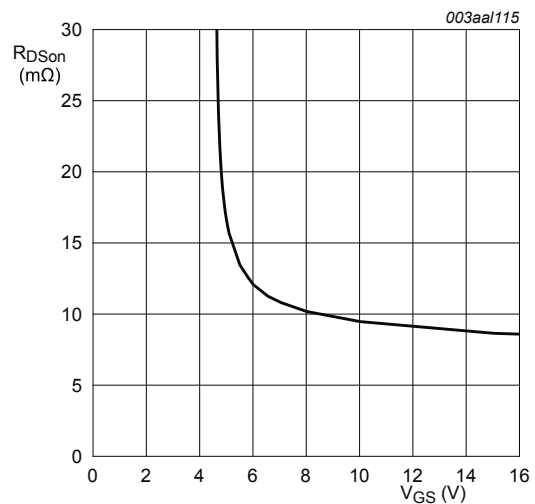
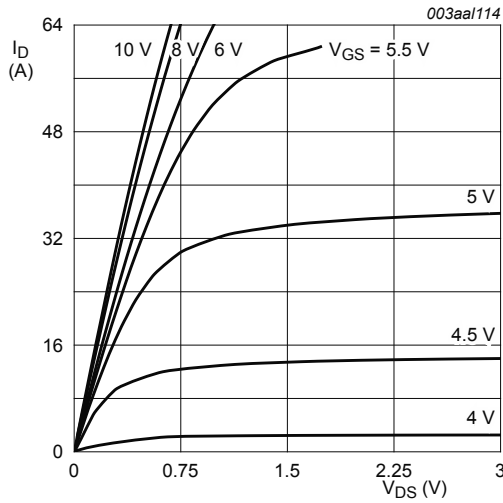


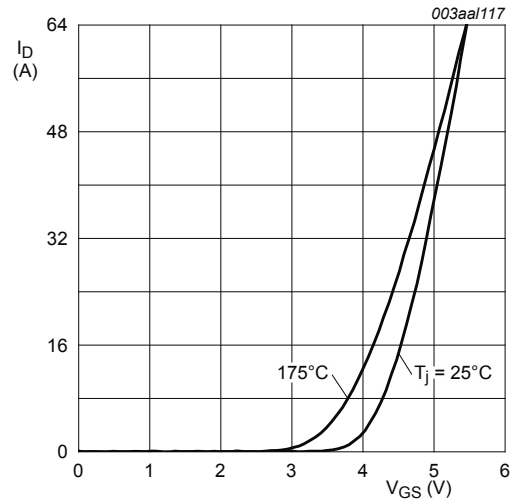
Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25^\circ\text{C}; I_D = 15\text{A}$



$T_j = 25\text{ }^\circ\text{C}; t_p = 300\text{ }\mu\text{s}$

Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values



$V_{DS} = 10\text{ V}$

Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

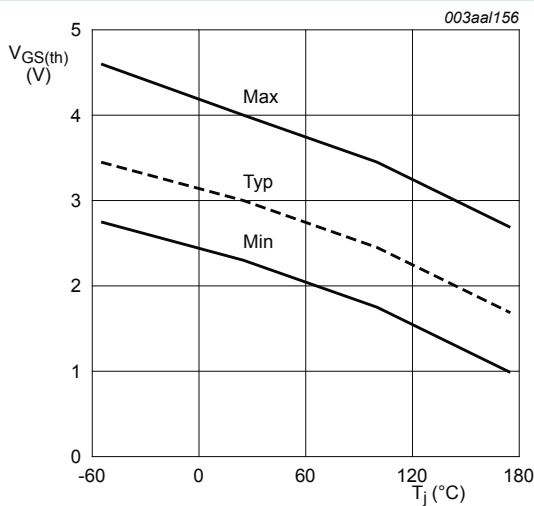
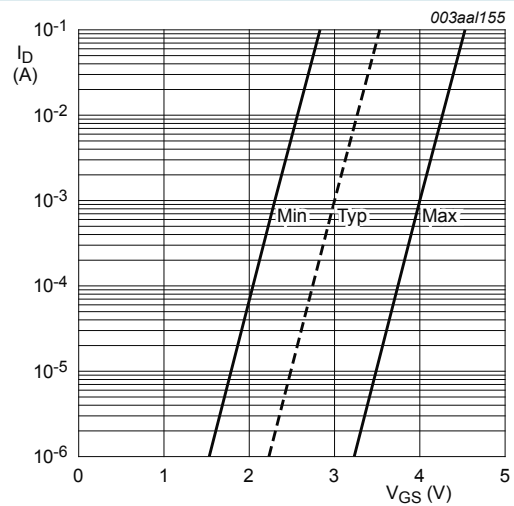


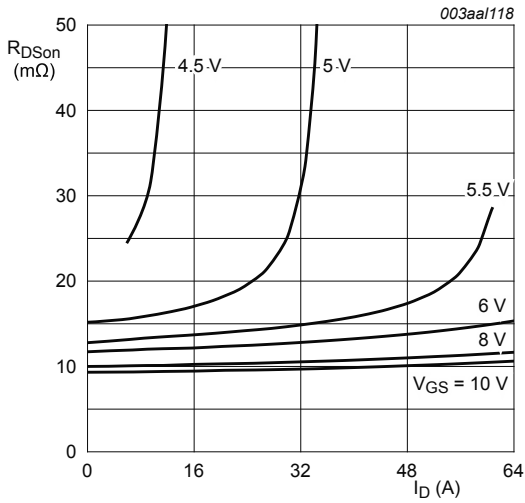
Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$



$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

Fig. 11. Sub-threshold drain current as a function of gate-source voltage



$T_j = 25^\circ\text{C}; t_p = 300 \mu\text{s}$

Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

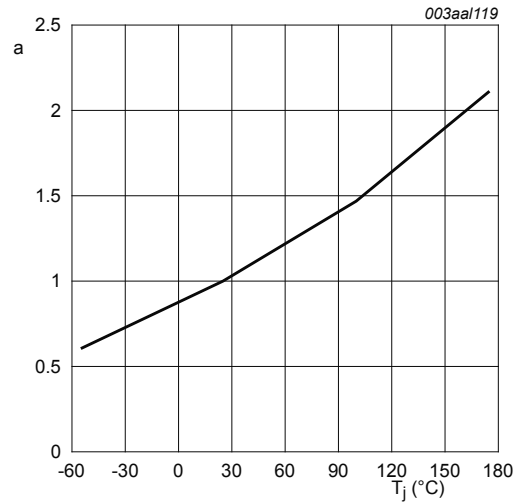


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25^\circ\text{C})}$$

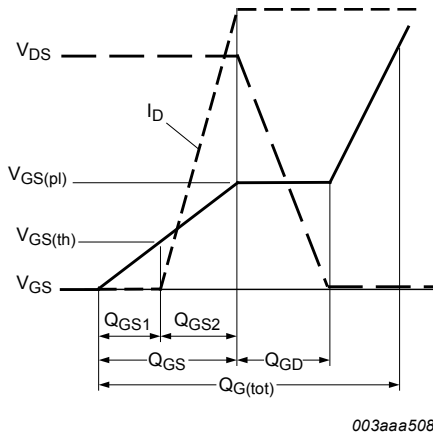


Fig. 14. Gate charge waveform definitions

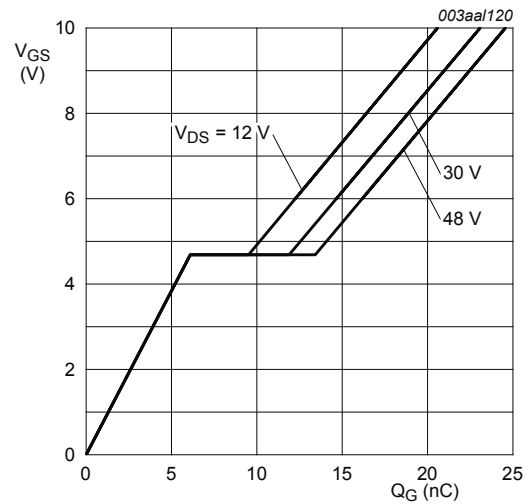


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^\circ\text{C}; I_D = 15\text{A}$

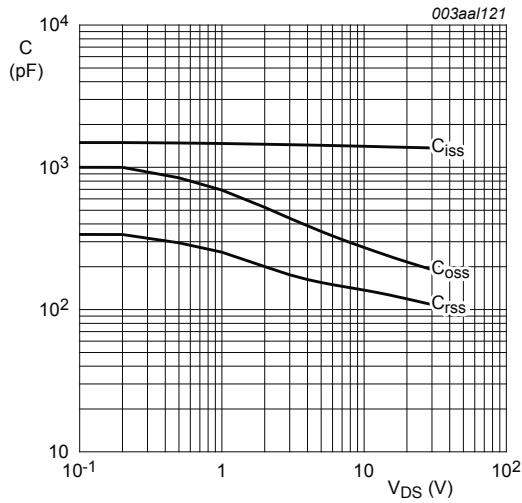


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

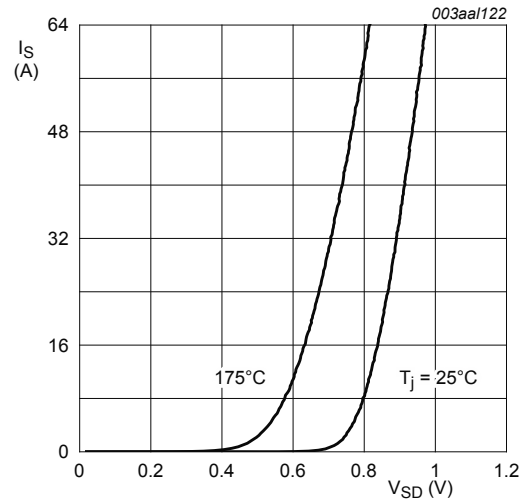


Fig. 17. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0V$$

11. Package outline

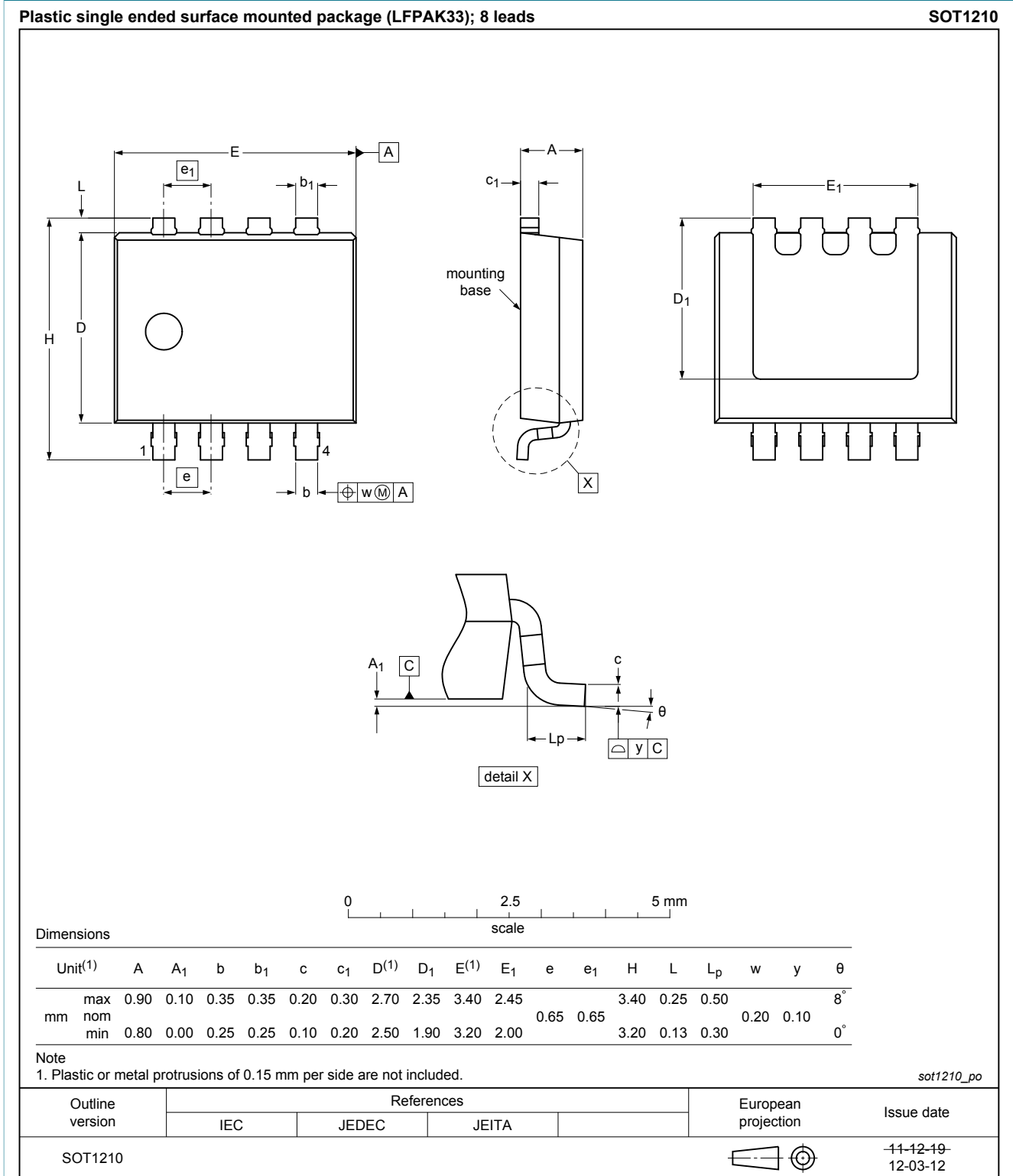


Fig. 18. Package outline LFAK33 (SOT1210)

12. Legal information

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Document status [1][2]	Product status [3]	Definition
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Product [short] data sheet	Production	This document contains the product specification.

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